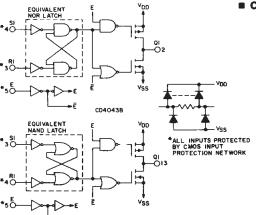


CMOS Quad 3-State **R/S Latches**

High-Voltage Types (20-Volt Rating) Quad NOR R/S Latch - CD4043B Quad NAND R/S Latch - CD4044B

CD4043B types are guad crosscoupled 3-state CMOS NOR latches and the CD4044B types are guad cross-coupled 3state CMOS NAND latches. Each latch has a separate Q output and individual SET and RESET inputs. The Q outputs are controlled by a common ENABLE input. A logic "1" or high on the ENABLE input connects the latch states to the Q outputs. A logic "0" or low on the ENABLE input disconnects the latch states from the Q outputs, resulting in an open circuit condition on the Q outputs. The open circuit feature allows common busing of the outputs.

The CD4043B and CD4044B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).



MAXIMUM RATINGS, Absolute-Maximum Values:

Fig. 1 - Logic diagrams.

CD40448

DC SUPPLY-VOLTAGE RANGE, (VDD)
Voltages referenced to V _{SS} Terminal)0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS0.5V to V _{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT
POWER DISSIPATION PER PACKAGE (PD):
For T _A = -55°C to +100°C
For T _A = +100°C to +125°C Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T _A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)
OPERATING-TEMPERATURE RANGE (T _A)
STORAGE TEMPERATURE RANGE (T _{stg})
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 \pm 1/32 inch (1.59 \pm 0.79mm) from case for 10s max

CD4043B, CD4044B Types

LATCH

LATCH

LATCH 3

LATCH

∎ VSS

FUNCTIONAL DIAGRAM

LATCH

LATCH

LATCH

LATCH

²-Oa

9-O 02

10 O o 1

004

13 ONC

92C5-2022IRI

13 O Q1

9.002

10 O 0 3

<u>'-0</u>04

ONC.

9205-2022

16 VDC

F5

13

12

11

IC Q3

9

OC* NC+

6

1 60

CD4044B

SREIO

+NO CHANGE

CD4044B

= \$4 R4

C ...

C 53

02

92C5-24477RI

s, 0.4

R, O-3

s₂ O-

R2 ()-7

\$3 O-12

R3 O-11

54 O¹

ENABLE O

R4 O-15

CD4043B

RIO-

\$10<u>3</u>

R2O-

s₂O<u>7</u>

R3O-12

\$30<u>11</u>

R4014

\$40<u>15</u>

NABLE O^{-5}

CD4044B FUNCTIONAL VSS

DIAGRAM

NC

SI

RI

R2

s2

Vss

NC = NO CONNECTION

***OPEN CIRCUIT**

ENABLE

Features:

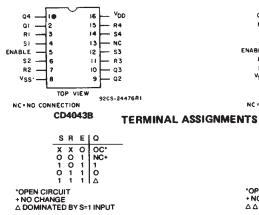
- 3-state outputs with common output ENABLE
- Separate SET and RESET inputs for each latch
- NOR and NAND configurations
- 5-V, 10-V, and 15-V parametric ratings
- Standardized symmetrical output characteristics
- 100% tested for guiescent current at 20 V
- Maximum input current of 1 µA at 18 V over full package temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package temperature range): $1 V \text{ at } V_{DD} = 5 V$ 2 V at Vpp = 10 V

2.5 V at
$$V_{DD}$$
 = 15 V

- Meets all requirements of JEDEC Tentative
- Standard No. 138, "Standard Specifications for Description of 'B' Series CMOS Devices'
- Applications:
- Holding register in multi-register system
- Four bits of independent storage with

Colorador a series

- output ENABLE
- Strobed register
- General digital logic
- CD4043B for positive logic systems
- CD4044B for negative logic systems



CD4043B

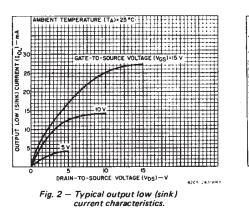
TRUTH TABLES

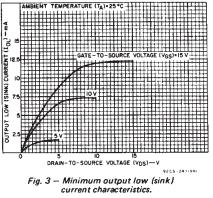
Recommended Operating Conditions T_A=25°C For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges.

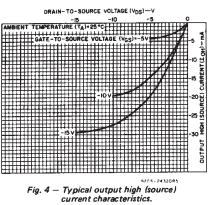
Characteristic 38	V _{DD} (V)	Min.	Max.	Units
Supply-Voltage Range (T _A = Full Package Temperature Range)	-	3	18	v
SET or RESET Pulse Width, t _W	5 10 15	160 80 40	-	ns

STATIC ELECTRICAL CHARACTERISTICS

CHARACTER	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)					C)					
ISTIC	Vo	VIN	VDD					+25			4			
	(V)	(V)	(V)	-55	-40	+85	+125	Min.	Тур.	Max.				
Quiescent Device Current, IDD Max.	-	0,5	5	1	1	30	30	_	0.02	1	μΑ			
	-	0,10	10	2	2	60	60	-	0.02	2				
	-	0,15	15	4	4	120	120	-	0.02	4				
	-	0,20	20	20	20	600	600	-	0.04	20				
Output Low (Sink) Current	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	-				
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	-				
IOL Min.	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	_				
Output High (Source) Current, IOH Min.	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	-	mA			
	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-				
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-				
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-				
Output Voltage: Low-Level,	-	0,5	5		0	.05		-	0	0.05				
		0,10	10	0.05				-	0	0.05	v			
VOL Max.		0,15	15	0.05				-	0	0.05				
Output Voltage:		0,5	5	4.95			4.95	5	-					
High-Level, VOH Min.	_	0,10	10	9.95			9.95	10	-					
	_	0,15	15	14.95			14.95	15	-					
Input Low Voltage, VIL Max.	0.5, 4.5	-	5	1.5				-	1.5					
	1, 9	-	10	3				—	3	1				
	1.5,13.5	-	15	4				-		4				
Input High Voltage, VIH Min.	0.5, 4.5	-	5	3.5			3.5	—	—	V.				
	1, 9	-	10	7				7	-	_]			
	1.5, 3.5	-	15	11				11		_				
Input Current IIN Max.	_	0,18	18	±0.1	±0.1	±1	±1	-	±10 ⁻⁵	±0.1	μΑ			
3-State Output Leakage Current IOUT Max.	0,18	0,18	18	±0.4	±0.4	±12	±12	_	±10-4	±0.4	μΑ			







DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^{\circ}$ C; Input t_r , $t_f = 20$ ns, $C_L = 50 \, pF$, $R_L = 200 \, K\Omega$

CHARACTERISTIC	V _{DD}	ALL		
· · · · · · · · · · · · · · · · · · ·	· (V)	TYP.	MAX.	1
Propagation Delay	5	150	300	
Time: tPHL, tPLH	10	70	140	ns
SET or RESET to Q	15	50	100	
3-State Propagation Delay	5	115	230	
Time: ENABLE to Q	10	55	110	ns
tPHZ, tPZH	15	40	80	
	5	90	180	
tPLZ, tPZL	10	50	100	.ns.
· · · · · · · · · · · · · · · · · · ·	15	35	70	
Transition Time:	5	100	200	
tTHL, tTLH	10	50	100	ns
	15	40	80	
Minimum	5	80	160	
SET or RESET	10	40	80	ns
Pulse Width, t _W	15	20	40	
Input Capacitance,	_	5	7.5	ρF
(Any Input) C _{IN}		l ĭ	1.0	

106

10

10

POWER (

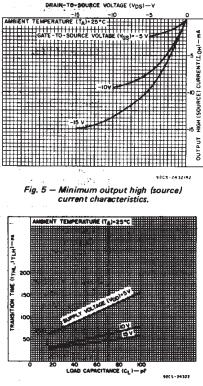


Fig. 6 — Typical transition time vs. load capacitance.

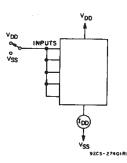
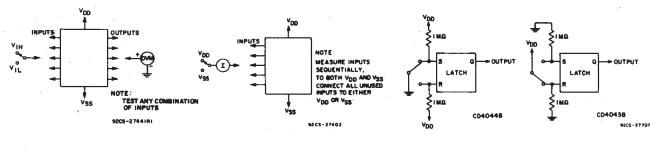


Fig. 9 - Quiescent device current.



TEST CIRCUITS

(TA)= 25

INPUT FREQUENCY-Hz

Fig. 8 – Typical power dissipation vs.

frequency.

9205-20201

ENT TEMPERATURE

Fig. 10 — Input voltage.

TEMPERATURE (TA)=25*C

OAD CAPA

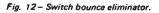
ČĒ (CL)

Fig. 7 — Typical propagation delay time vs. load capacitance—SET, RESET to Q, Q.

9205-2770

GATION DEL

Fig. 11 - Input current.



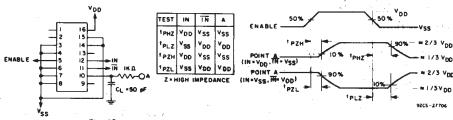
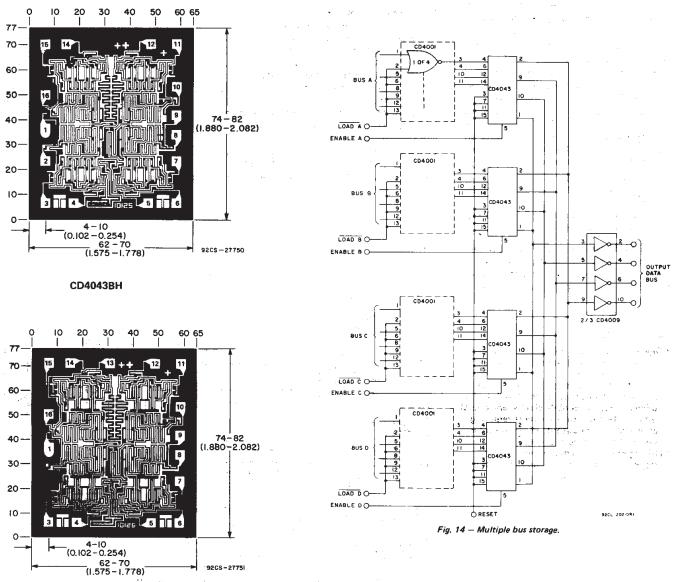


Fig. 13 - ENABLE propagation delay time test circuit and waveforms.

4

. 42

CHIP DIMENSIONS AND PAD LAYOUTS



3

COMMERCIAL CMOS

HIGH VOLTAGE ICs



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch) .

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 1999, Texas Instruments Incorporated